

/ Descriptions

KF \$0) GE G Silicon PNP transistor in a TO-92 Plastic Package.

/ Features

Low noise, high DC current gain, high breakdown voltage.

/ Applications

Low noise audio amplifier applications.

/ Equivalent Circuit



/ Pinning



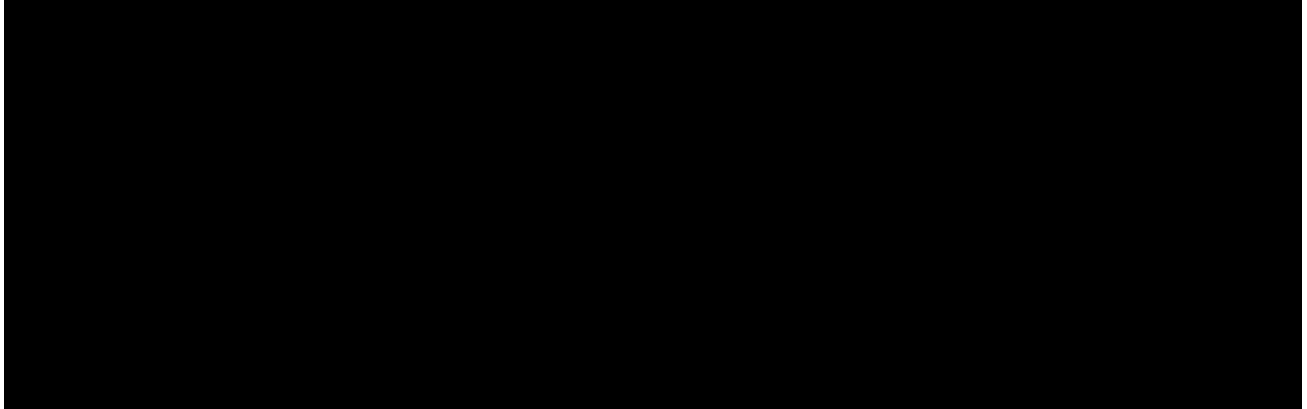
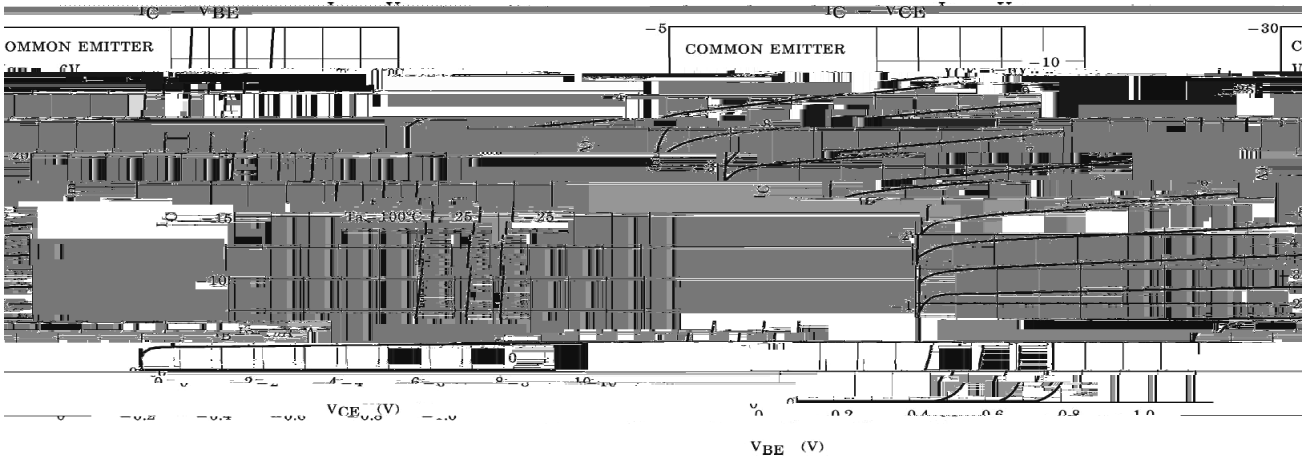
PIN1 Base PIN 2 Collector PIN 3 Emitter

/ hFE Classifications & Marking

h _{FE} Classifications Symbol	GR	BL
h _{FE} Range	200~400	350~700

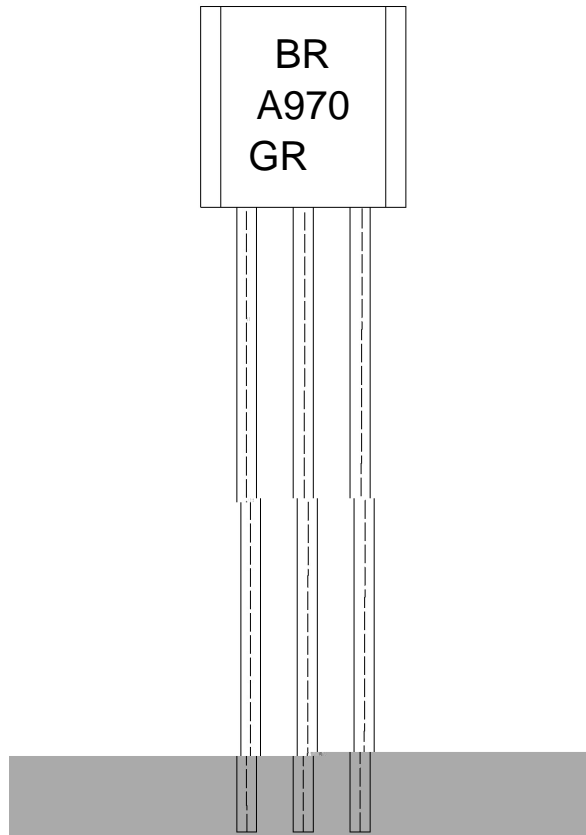
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	-120	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Emitter Current – Continuous	I_E	100	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	152 591iw560.J/TT7 161 Tf28 TD0107	

/ Electrical Characteristic Curve



2SA970
Rev.E Mar.-2016

/ Marking Instructions



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Note:

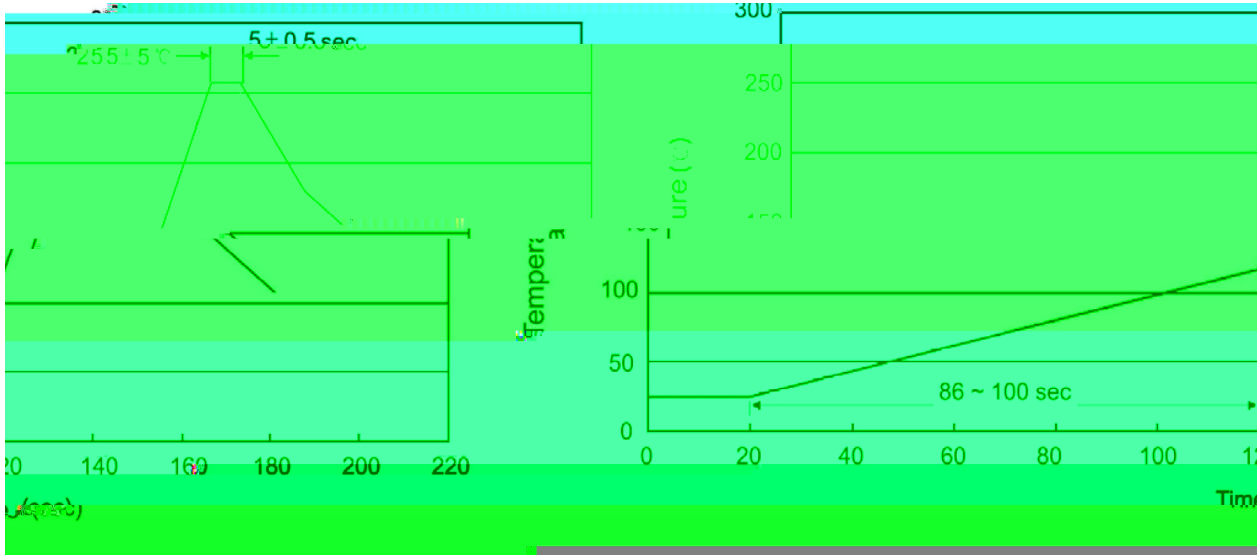
BR: Company Code.

A970: Product Type Code.

GR: h_{FE} Classifications Symbol

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | |
|---|----------|-------------|--|
| 1 | 25 ~ 150 | 60 ~ 90sec; | 1. Preheating: 25~150 , Time: 60~90sec. |
| 2 | 255 ± 5 | 5 ± 0.5sec; | 2. Peak Temp.: 255 ± 5 , Duration: 5 ± 0.5sec. |
| 3 | 2 ~ 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270 ± 5 10 ± 1 sec. Temp: 270 ± 5 Time: 10 ± 1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units				Dimension			(unit mm ³)

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